

General Description

The HSM0026 is the high cell density trenched N-ch MOSFETs, which provide excellent R_{DS(on)} and gate charge for most of the synchronous buck converter applications.

The HSM0026 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

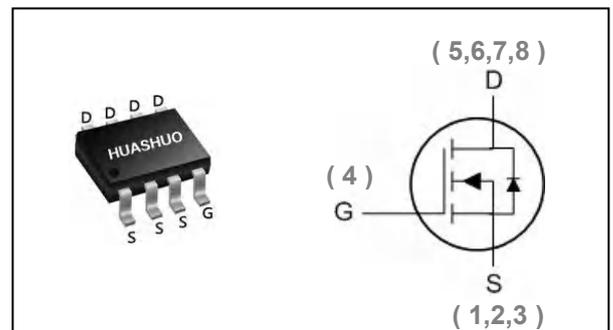
Features

- Green Device Available
- Super Low Gate Charge
- Excellent C_{dv/dt} effect decline
- Advanced high cell density Trench Technology

Product Summary

V _{DS}	100	V
R _{DS(ON),max}	20	mΩ
I _D	7.5	A

SOP8 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	100	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _A =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	7.5	A
I _D @T _A =70°C	Continuous Drain Current, V _{GS} @ 10V ¹	6	A
I _{DM}	Pulsed Drain Current ²	40	A
EAS	Single Pulse Avalanche Energy ³	16	mJ
I _{AS}	Avalanche Current	18	A
P _D @T _A =25°C	Total Power Dissipation ⁴	2.5	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-ambient ¹ (t ≤ 10S)	---	50	°C/W
	Thermal Resistance Junction-ambient ¹ (Steady State)	---	85	°C/W



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	100	---	---	V
ΔBV _{DSS} /ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.08	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =7A	---	16	20	mΩ
		V _{GS} =4.5V, I _D =5A	---	19	25	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.2	2.0	2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-5.5	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =80V, V _{GS} =0V, T _J =25°C	---	---	10	uA
		V _{DS} =80V, V _{GS} =0V, T _J =55°C	---	---	100	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =7A	---	24	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	1.6	---	Ω
Q _g	Total Gate Charge (10V)	V _{DS} =80V, V _{GS} =10V, I _D =7A	---	36	---	nC
Q _{gs}	Gate-Source Charge		---	5	---	
Q _{gd}	Gate-Drain Charge		---	10	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =50V, V _{GS} =10V, R _G =3.3Ω I _D =7A	---	11.5	---	ns
T _r	Rise Time		---	29	---	
T _{d(off)}	Turn-Off Delay Time		---	42	---	
T _f	Fall Time		---	18	---	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	1930	---	pF
C _{oss}	Output Capacitance		---	245	---	
C _{rss}	Reverse Transfer Capacitance		---	125	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,6}	V _G =V _D =0V, Force Current	---	---	7	A
I _{SM}	Pulsed Source Current ^{2,6}		---	---	40	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V
t _{rr}	Reverse Recovery Time	IF=7A, di/dt=100A/μs, T _J =25°C	---	48	---	nS
Q _{rr}	Reverse Recovery Charge		---	29	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



Typical Characteristics

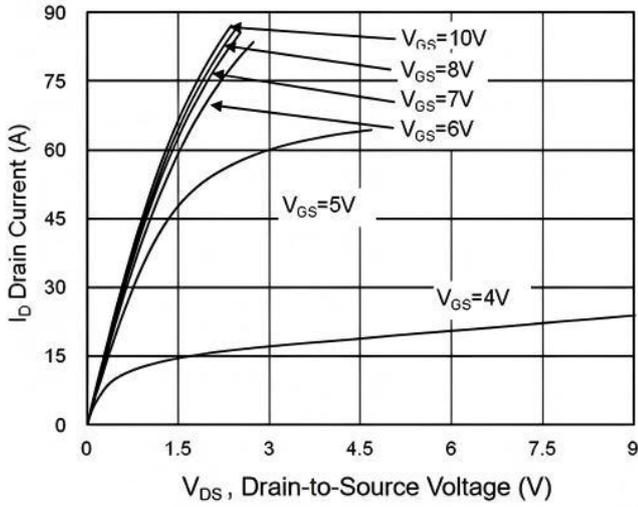


Fig.1 Typical Output Characteristics

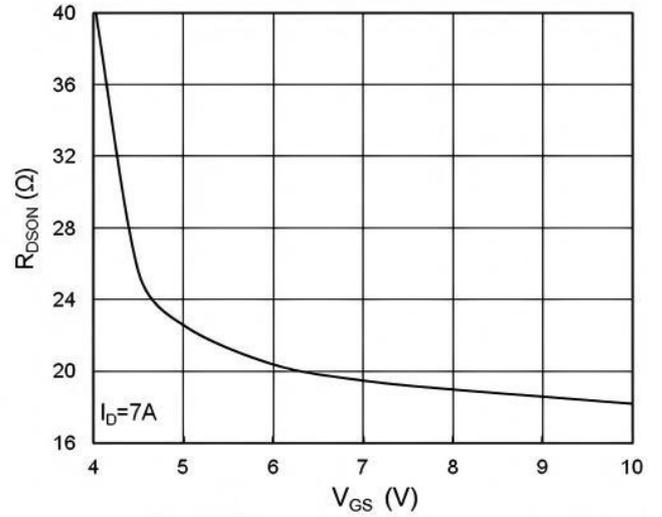


Fig.2 On-Resistance vs. Gate-Source

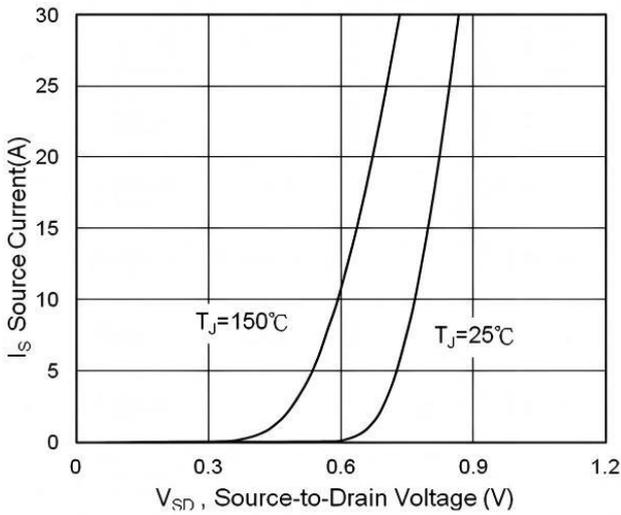


Fig.3 Forward Characteristics Of Reverse diode

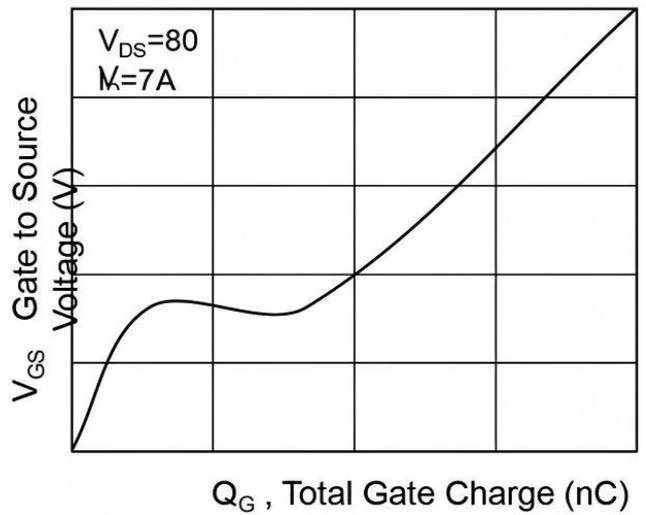


Fig.4 Gate-Charge Characteristics

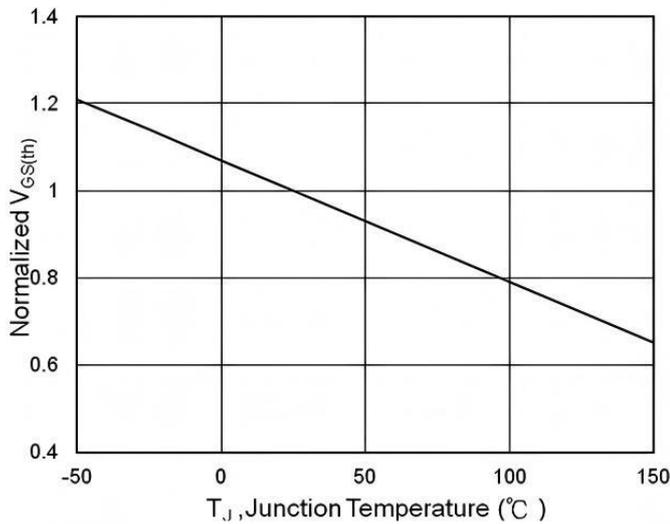


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

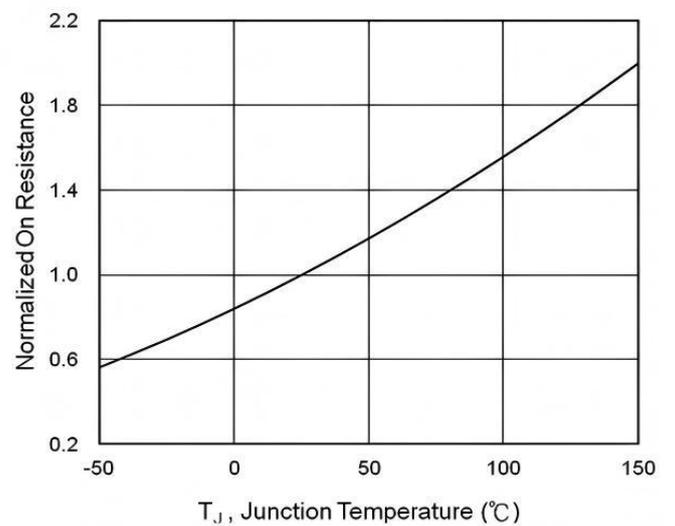


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

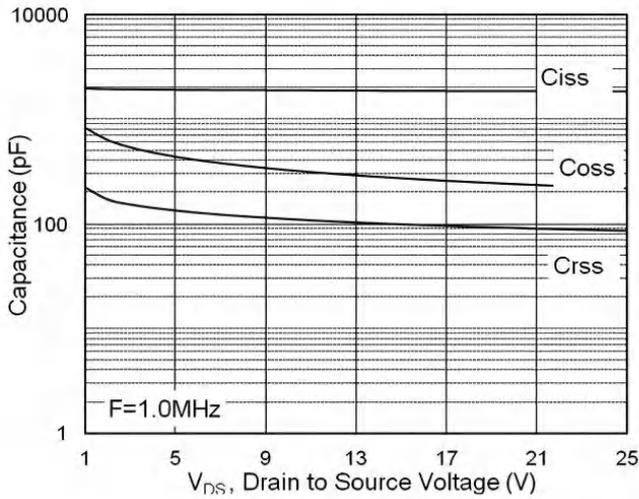


Fig.7 Capacitance

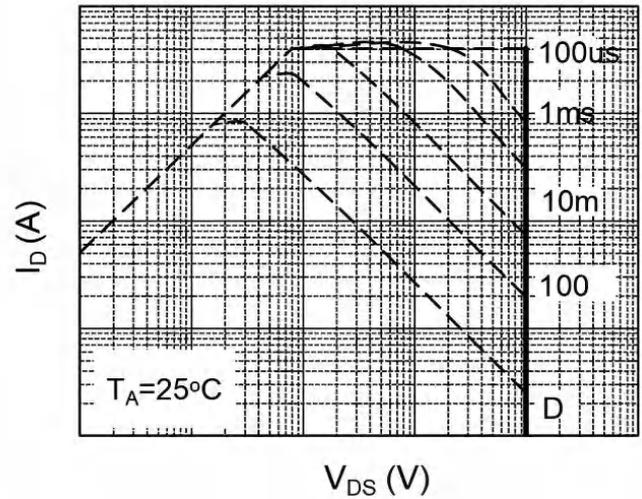


Fig.8 Safe Operating Area

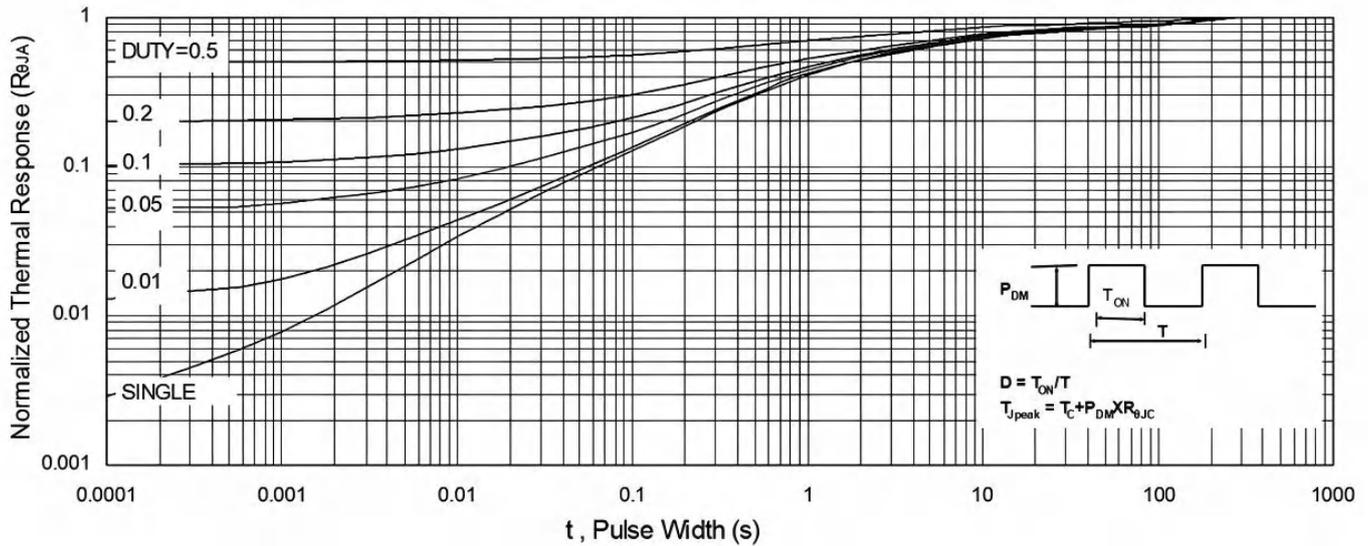


Fig.9 Normalized Maximum Transient Thermal Impedance

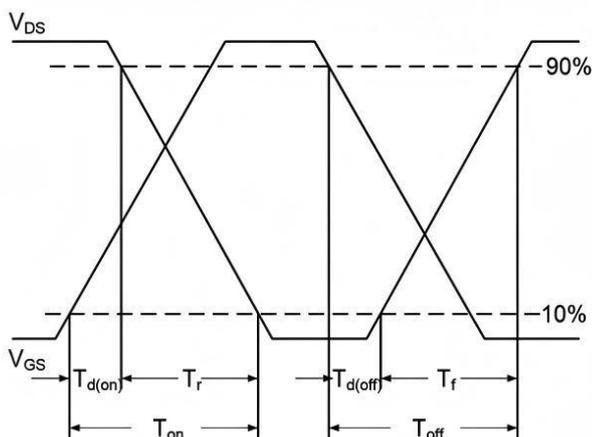


Fig.10 Switching Time Waveform

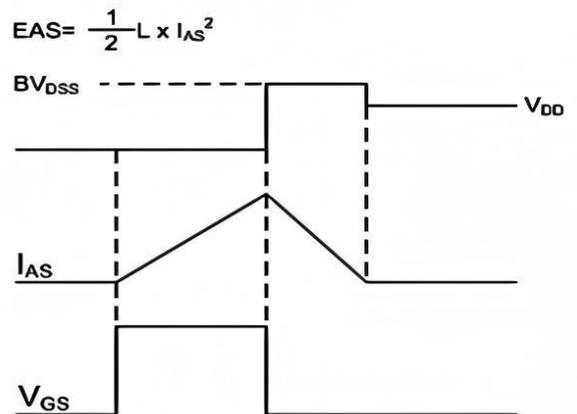


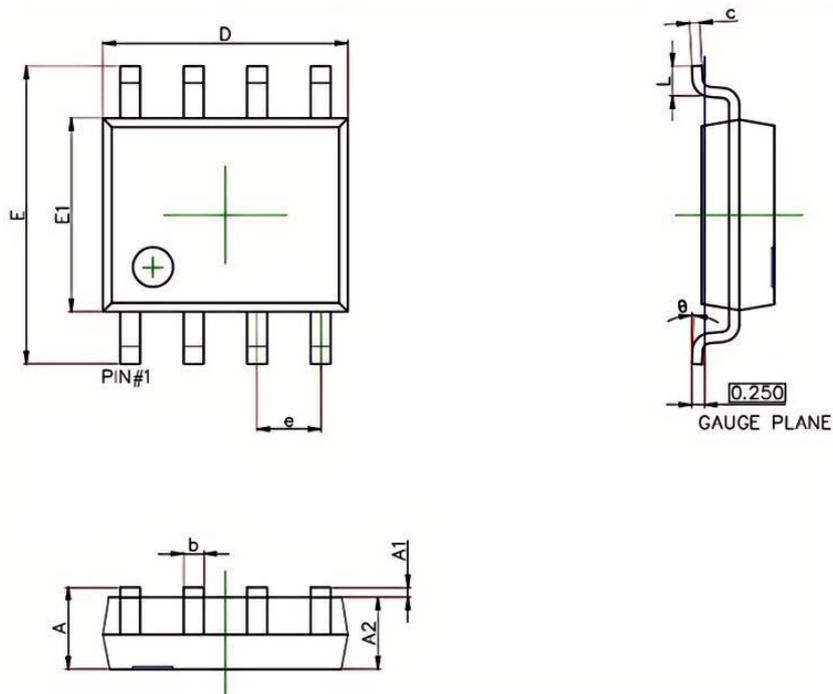
Fig.11 Unclamped Inductive Switching Waveform



Ordering Information

Part Number	Package code	Packaging
HSM0026	SOP-8	2500/Tape&Reel

SOP-8 Package Outline



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
C	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270 (BSC)		0.050(BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



HSM0026 Marking:

